which is the same as the Fermi-Dirac distribution function derived in Chapter 7. We substitute (68) in (69) to obtain

$$f = \frac{1}{(n_Q \tau/p) \exp(\varepsilon/\tau) + 1} = \frac{p}{n_Q \tau \exp(\varepsilon/\tau) + p} , \qquad (70)$$

or, with $p_0 \equiv n_0 \tau \exp(\varepsilon/\tau)$,

$$f = \frac{p}{p_0 + p} \,, \tag{71}$$

where p_0 is constant with respect to pressure, but depends on the temperature. The result (71) is known as the Langmuir adsorption isotherm when used to describe the adsorption of gases on the surfaces of solids.

Example: Impurity atom ionization in a semiconductor. Atoms of numerous chemical elements when present as impurities in a semiconductor may lose an electron by ionization to the conduction band of the semiconductor crystal. In the conduction band the electron moves about much as if it were a free particle, and the electron gas in the conduction band may often be treated as an ideal gas. The impurity atoms are small systems & in thermal and diffusive equilibrium with the large reservoir formed by the rest of the semiconductor; the atoms exchange electrons and energy with the semiconductor.

Let I be the ionization energy of the impurity atom. We suppose that one, but only one, electron can be bound to an impurity atom; either orientation \uparrow or \downarrow of the electron spin is accessible. Therefore the system \mathcal{S} has three allowed states—one without an electron, one with an electron attached with spin \uparrow , and one with an electron attached with spin \downarrow . When \mathcal{S} has zero electrons, the impurity atom is ionized. We choose the zero of energy of \mathcal{S} as this state; the other two states therefore have the common energy $\varepsilon = -I$. The accessible states of \mathcal{S} are summarized below.

State number	Description	N	3
1	Electron detached	0	0
2	Electron attached, spin ↑	1	-I
3	Electron attached, spin ↓	1	-I

The Gibbs sum is given by

$$\mathcal{F} = 1 + 2 \exp[(\mu + I)/\tau].$$
 (72)

